

Silicon NPN transistor in a TO-252 Plastic Package.

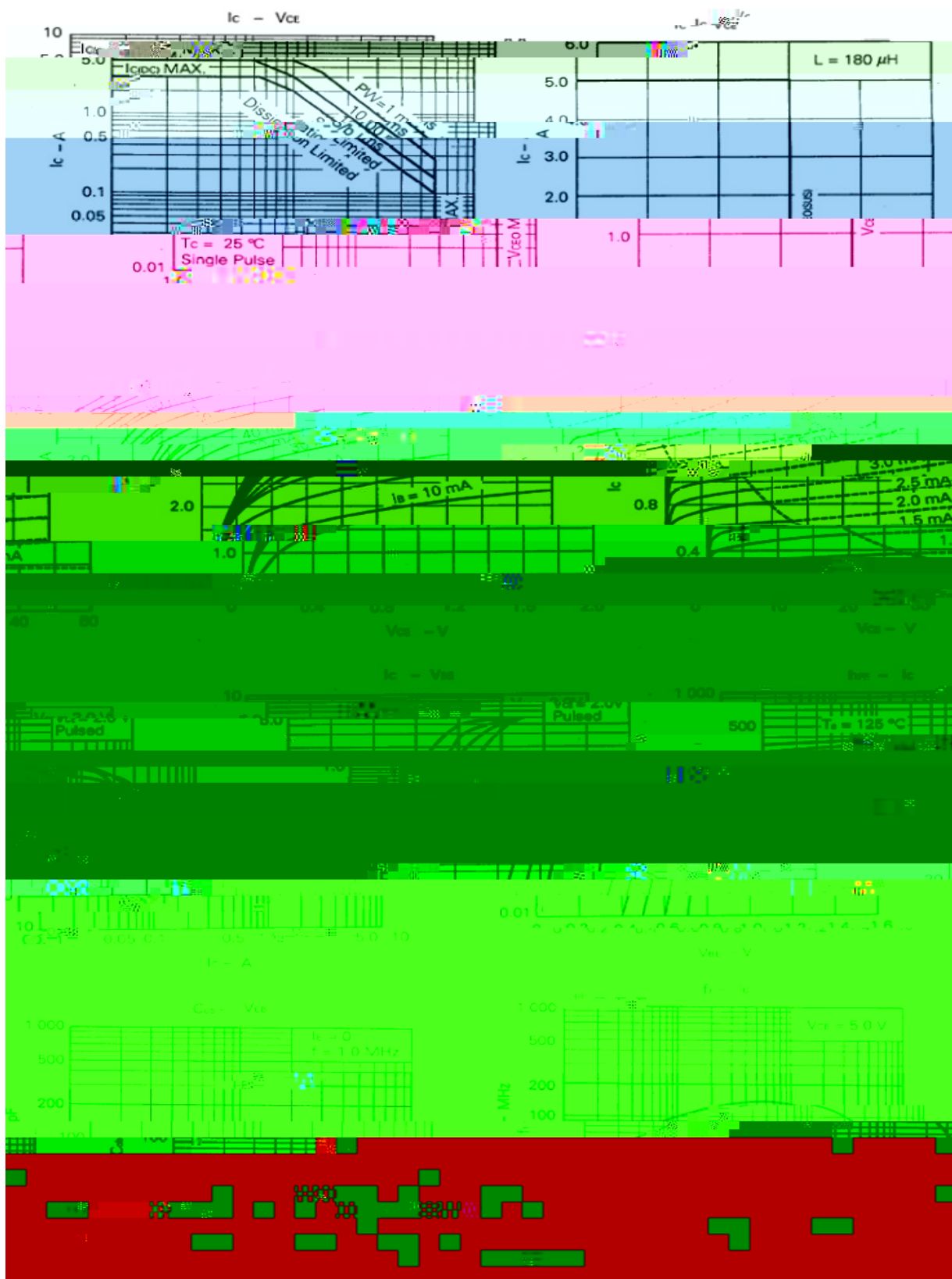
Low $V_{CE(sat)}$, 10.5 62.94 731.2403 Tm-0.0002 Tc β 03a47.30203 Tm-0.0009 T2dirent and 009 Tf0.5 6(at)-5.1())T2T

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation*	$*P_C$	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

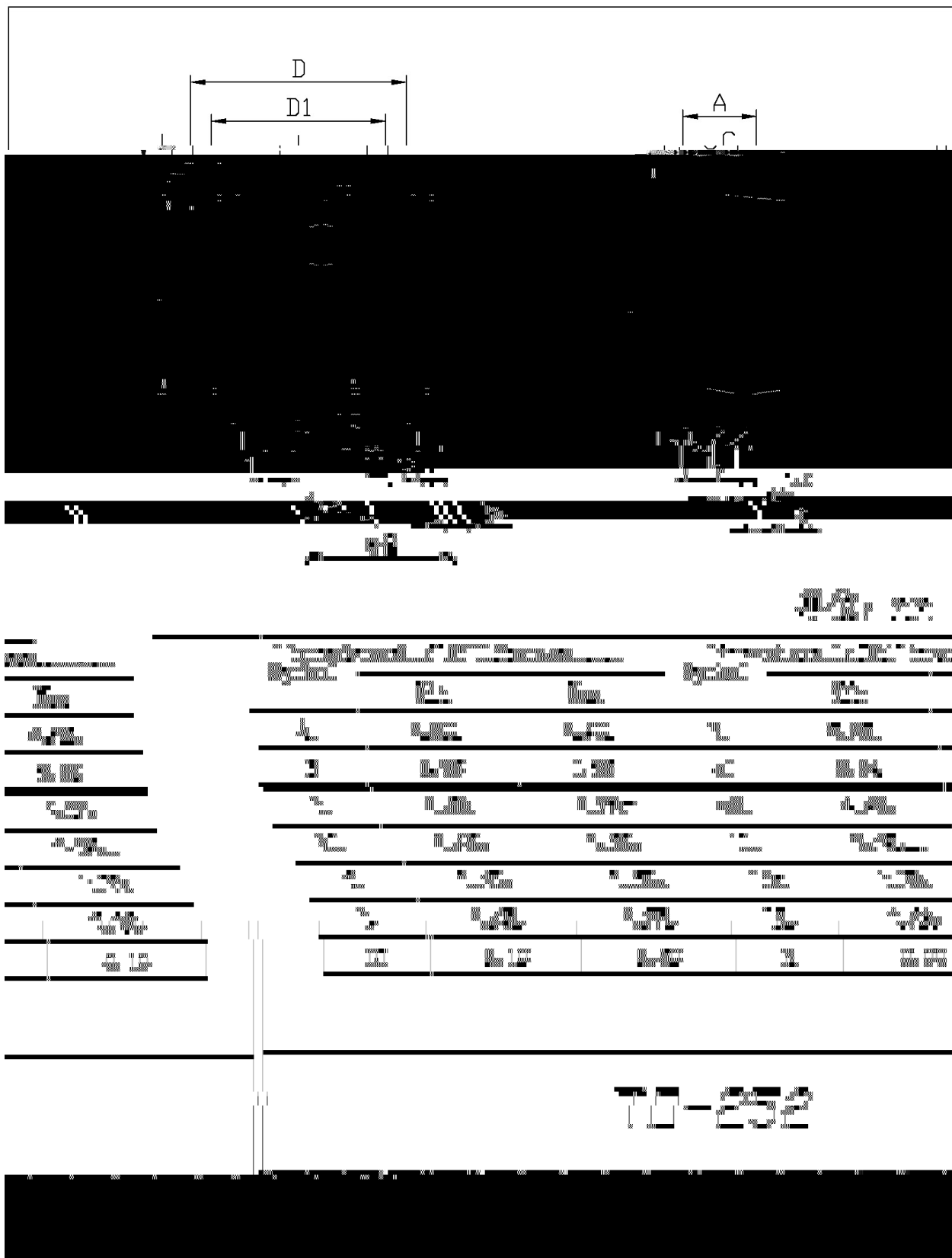
*When mounted on a 7.5×7.5×0.7mm ceramic board

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\mu A$ $I_E=0$	60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	60			V

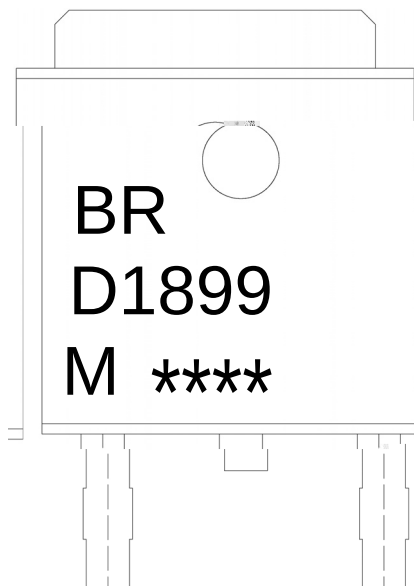
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

h_{FE}

Note:

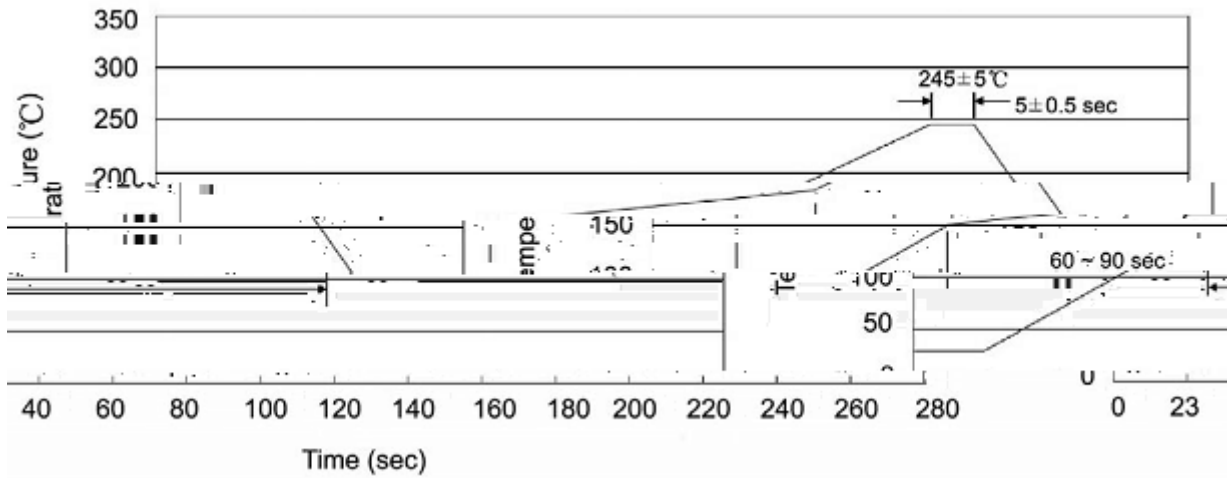
BR: Company Code

D1899: Product Type.

M: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / **Temperature Profile for IR Reflow Soldering(Pb-Free)**



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ **Resistance to Soldering Heat Test Conditions**

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ **Packaging SPEC.**

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	5	25,000	13 ×16	360×360×50	385×257×392

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180